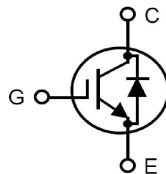


# High Voltage XPT™ IGBT w/ Diode

## IXYX25N250CV1 IXYX25N250CV1HV

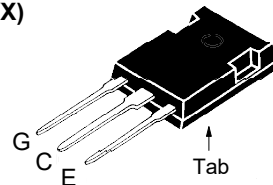
$V_{CES} = 2500V$   
 $I_{C110} = 25A$   
 $V_{CE(sat)} \leq 4.0V$   
 $t_{fi(typ)} = 246ns$



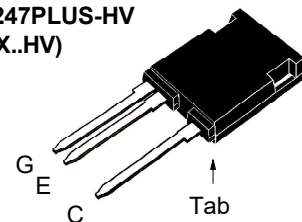
Symbol	Test Conditions	Maximum Ratings	
$V_{CES}$	$T_J = 25^\circ C$ to $175^\circ C$	2500	V
$V_{CGR}$	$T_J = 25^\circ C$ to $175^\circ C$ , $R_{GE} = 1M\Omega$	2500	V
$V_{GES}$	Continuous	$\pm 20$	V
$V_{GEM}$	Transient	$\pm 30$	V
$I_{C25}$	$T_C = 25^\circ C$	95	A
$I_{C110}$	$T_C = 110^\circ C$	25	A
$I_{F110}$	$T_C = 110^\circ C$	30	A
$I_{CM}$	$T_C = 25^\circ C$ , 1ms	235	A
<b>SSOA</b> <b>(RBSOA)</b>	$V_{GE} = 15V$ , $T_{VJ} = 150^\circ C$ , $R_G = 5\Omega$ Clamped Inductive Load	$I_{CM} = 100$ 1500	A V
$P_C$	$T_C = 25^\circ C$	937	W
$T_J$		-55 ... +175	$^\circ C$
$T_{JM}$		175	$^\circ C$
$T_{stg}$		-55 ... +175	$^\circ C$
$T_L$	Maximum Lead Temperature for Soldering 1.6 mm (0.062in.) from Case for 10s	300	$^\circ C$
$F_C$	Mounting Force	20..120 /4.5..27	N/lb
<b>Weight</b>		6	g

Symbol	Test Conditions ( $T_J = 25^\circ C$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{CES}$	$I_C = 250\mu A$ , $V_{GE} = 0V$	2500		V
$V_{GE(th)}$	$I_C = 250\mu A$ , $V_{CE} = V_{GE}$	3.0		V
$I_{CES}$	$V_{CE} = V_{CES}$ , $V_{GE} = 0V$ $T_J = 100^\circ C$		100	25 $\mu A$ $\mu A$
$I_{GES}$	$V_{CE} = 0V$ , $V_{GE} = \pm 20V$			$\pm 100$ nA
$V_{CE(sat)}$	$I_C = 25A$ , $V_{GE} = 15V$ , Note 1 $T_J = 150^\circ C$		3.4 4.7	V V

PLUS247  
(IXYX)



TO-247PLUS-HV  
(IXYX..HV)



G = Gate                      E = Emitter  
 C = Collector                Tab = Collector

### Features

- High Voltage Packages
- High Blocking Voltage
- High Peak Current Capability
- Low Saturation Voltage

### Advantages

- Low Gate Drive Requirement
- High Power Density

### Applications

- Switch-Mode and Resonant-Mode Power Supplies
- Uninterruptible Power Supplies (UPS)
- Laser Generators
- Capacitor Discharge Circuits
- AC Switches

Symbol Test Conditions ( $T_J = 25^\circ\text{C}$ Unless Otherwise Specified)		Characteristic Values		
		Min.	Typ.	Max.
$g_{fs}$	$I_C = 25\text{A}, V_{CE} = 10\text{V}$ , Note 1	16	27	S
$R_{Gi}$	Gate Input Resistance		2.8	$\Omega$
$C_{ies}$	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$		3060	pF
$C_{oes}$			166	pF
$C_{res}$			43	pF
$Q_{g(on)}$	$I_C = 25\text{A}, V_{GE} = 15\text{V}, V_{CE} = 0.5 \cdot V_{CES}$		147	nC
$Q_{ge}$			16	nC
$Q_{gc}$			68	nC
$t_{d(on)}$	<b>Inductive load, <math>T_J = 25^\circ\text{C}</math></b> $I_C = 25\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 0.5 \cdot V_{CES}, R_G = 5\Omega$ Note 2		15	ns
$t_{ri}$			34	ns
$E_{on}$			8.3	mJ
$t_{d(off)}$			230	ns
$t_{fi}$			246	ns
$E_{off}$			7.3	mJ
$t_{d(on)}$	<b>Inductive load, <math>T_J = 150^\circ\text{C}</math></b> $I_C = 25\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 0.5 \cdot V_{CES}, R_G = 5\Omega$ Note 2		18	ns
$t_{ri}$			33	ns
$E_{on}$			11.0	mJ
$t_{d(off)}$			225	ns
$t_{fi}$			350	ns
$E_{off}$			10.5	mJ
$R_{thJC}$				0.16 $^\circ\text{C/W}$
$R_{thCS}$		0.15		$^\circ\text{C/W}$

### Reverse Sonic Diode (FRD)

Symbol Test Conditions ( $T_J = 25^\circ\text{C}$ Unless Otherwise Specified)		Characteristic Values		
		Min.	Typ.	Max.
$V_F$	$I_F = 25\text{A}, V_{GE} = 0\text{V}$ , Note 1 $T_J = 150^\circ\text{C}$		3.1	3.5 V V
$I_{RM}$	$I_F = 25\text{A}, V_{GE} = 0\text{V}, T_J = 150^\circ\text{C}$ $-di_F/dt = 500\text{A}/\mu\text{s}, V_R = 1200\text{V}$		38	A
$t_{rr}$			185	ns
$R_{thJC}$				0.32 $^\circ\text{C/W}$

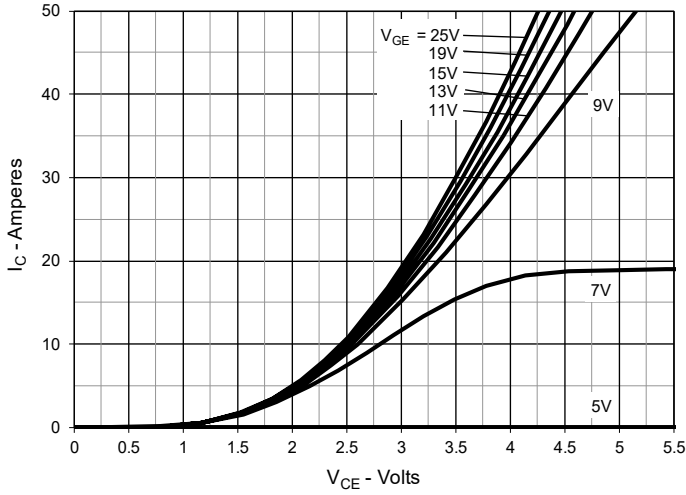
#### Notes:

1. Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .
2. Switching times & energy losses may increase for higher  $V_{CE}$  (Clamp),  $T_J$  or  $R_G$ .

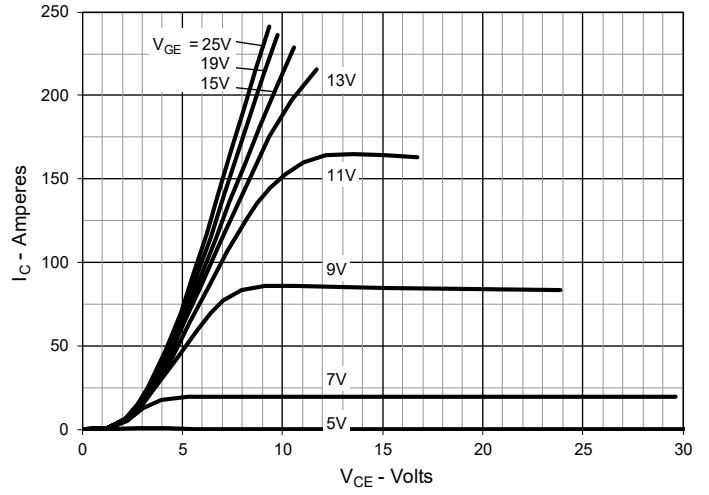
Littelfuse reserves the right to change limits, test conditions, and dimensions.

LF MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338 B2
	4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

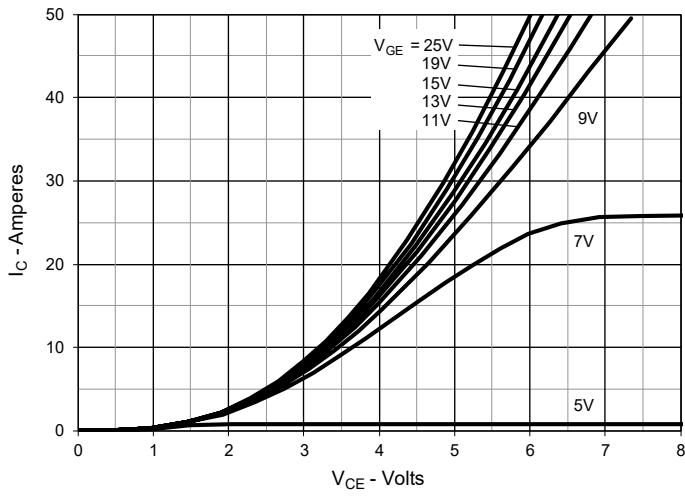
**Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$**



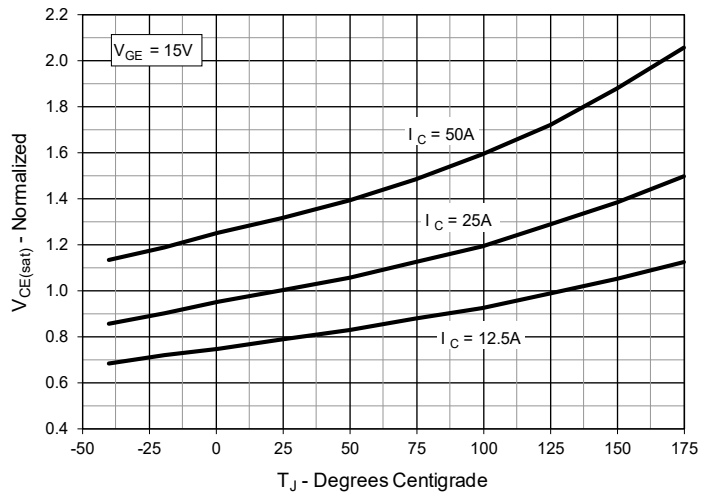
**Fig. 2. Extended Output Characteristics @  $T_J = 25^\circ\text{C}$**



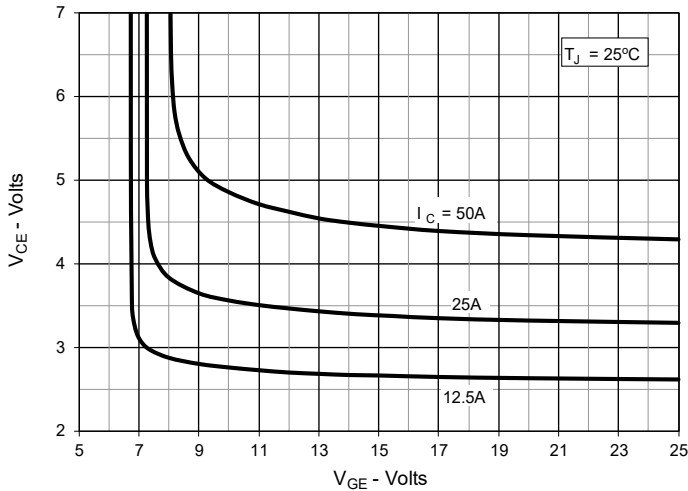
**Fig. 3. Output Characteristics @  $T_J = 150^\circ\text{C}$**



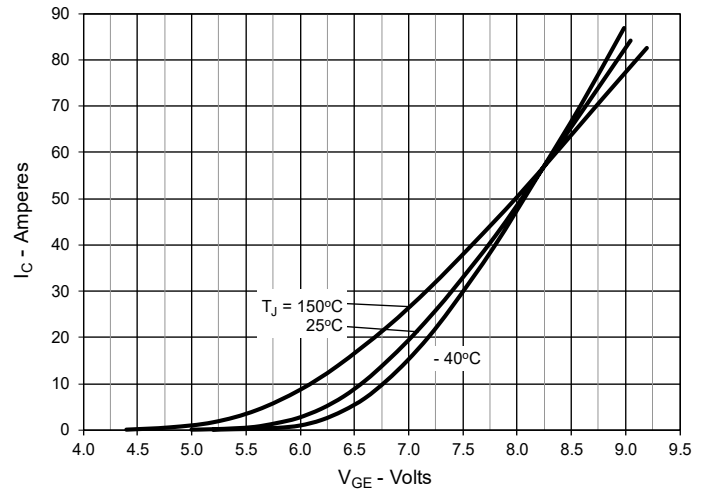
**Fig. 4. Dependence of  $V_{CE(sat)}$  on Junction Temperature**



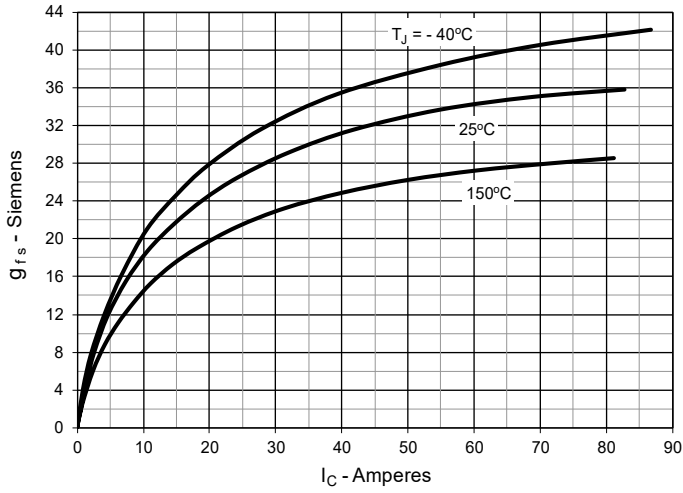
**Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage**



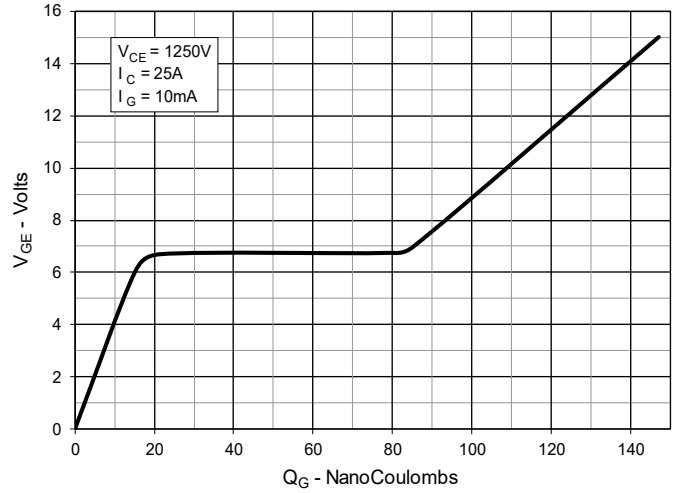
**Fig. 6. Input Admittance**



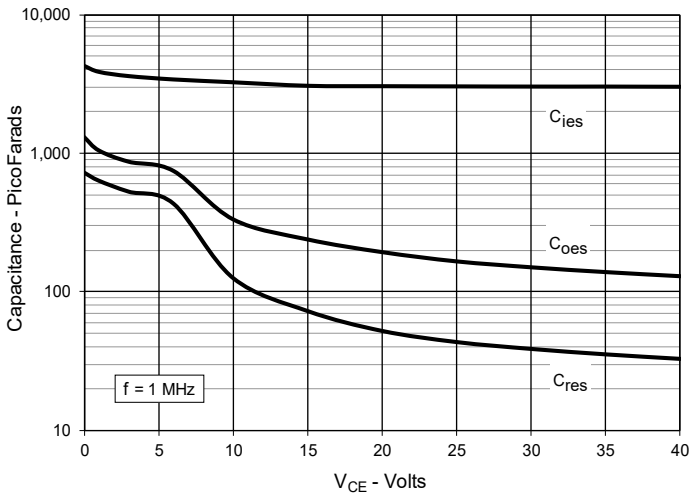
**Fig. 7. Transconductance**



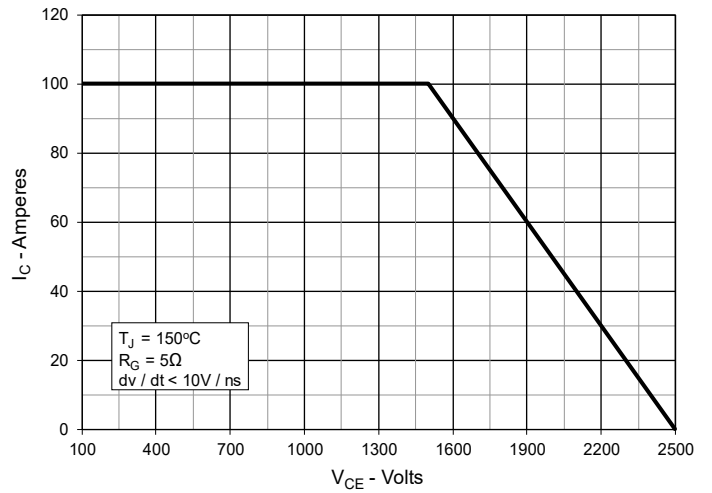
**Fig. 8. Gate Charge**



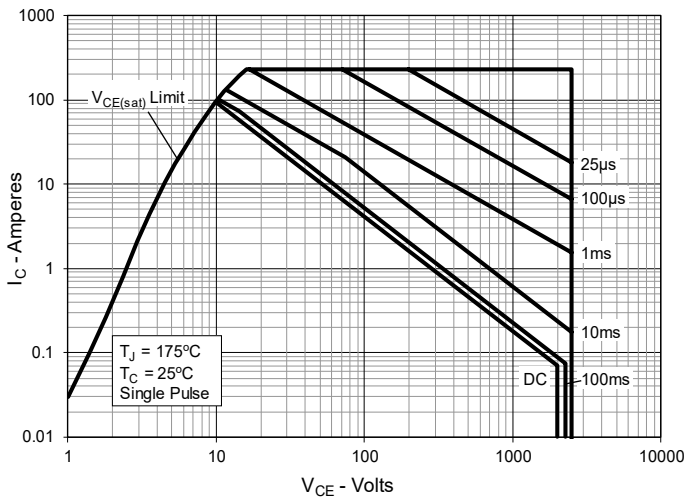
**Fig. 9. Capacitance**



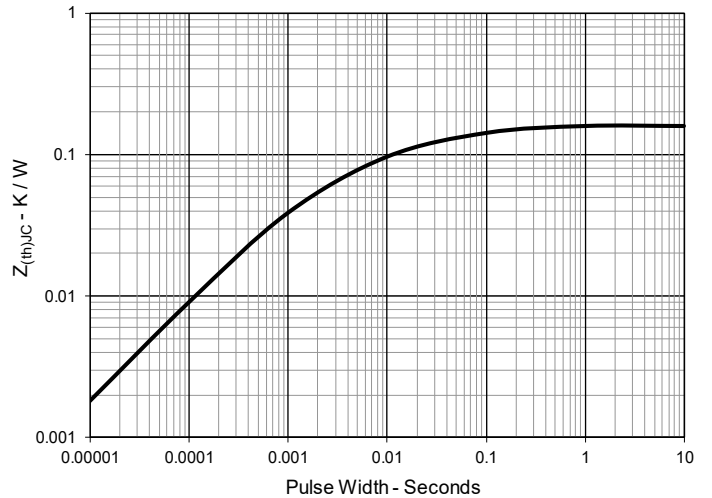
**Fig. 10. Reverse-Bias Safe Operating Area**



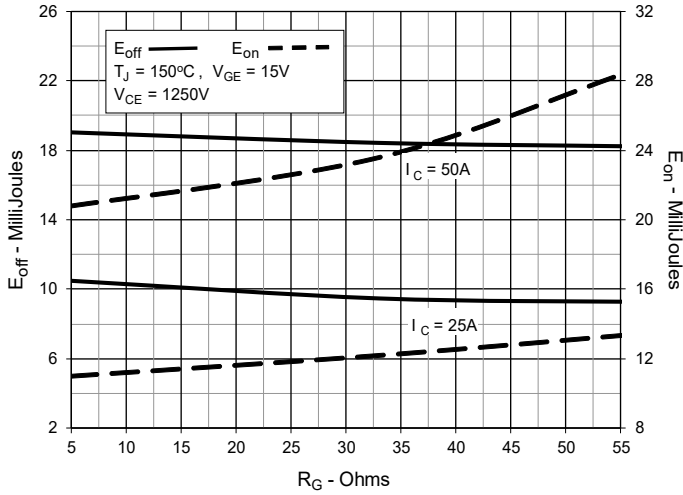
**Fig. 11. Forward-Bias Safe Operating Area**



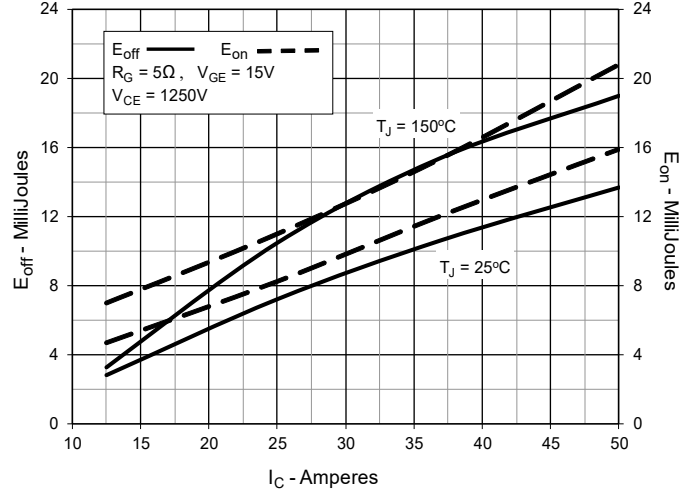
**Fig. 12. Maximum Transient Thermal Impedance**



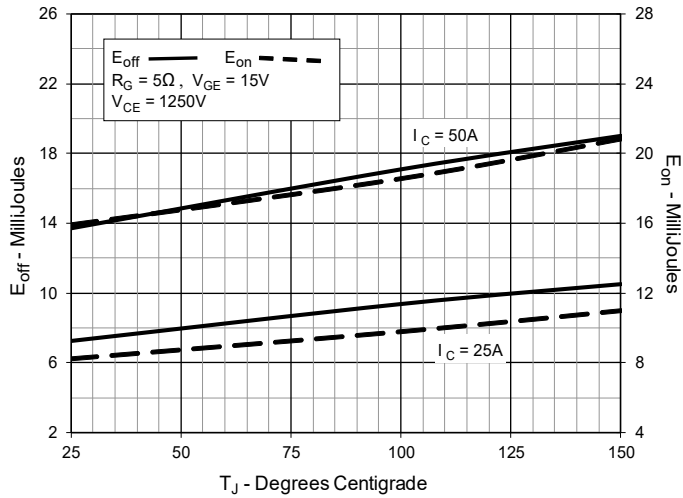
**Fig. 13. Inductive Switching Energy Loss vs. Gate Resistance**



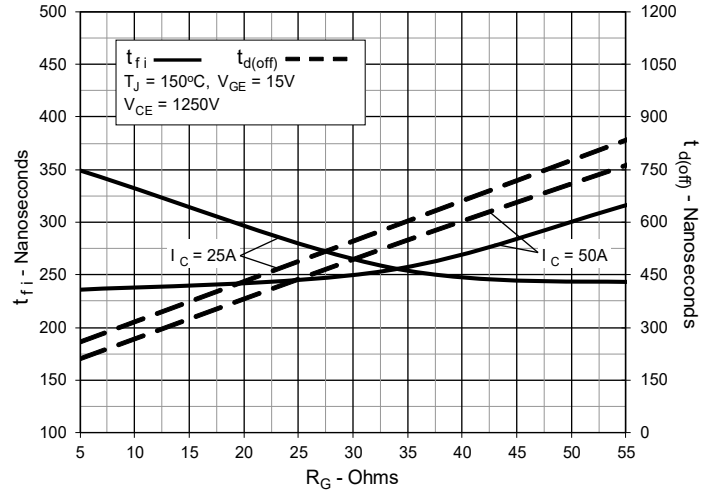
**Fig. 14. Inductive Switching Energy Loss vs. Collector Current**



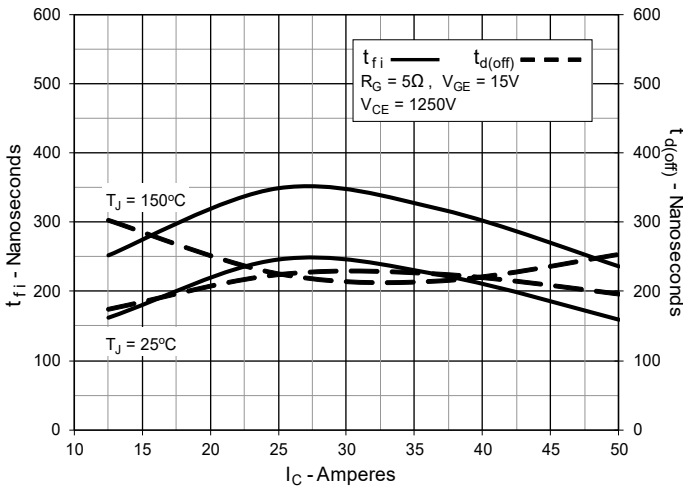
**Fig. 15. Inductive Switching Energy Loss vs. Junction Temperature**



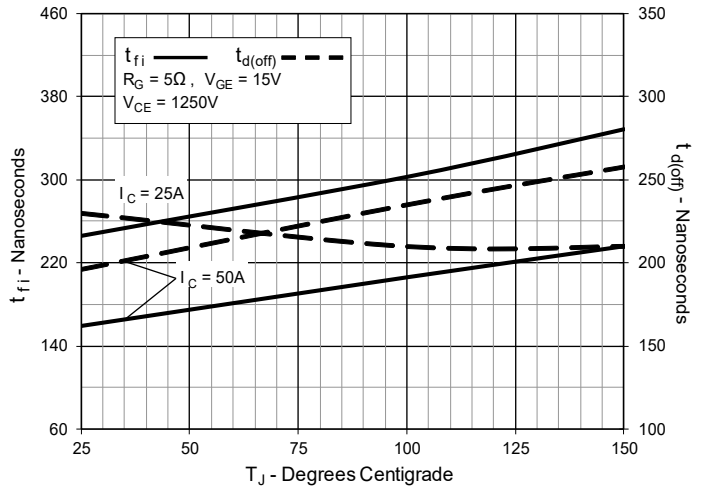
**Fig. 16. Inductive Turn-off Switching Times vs. Gate Resistance**



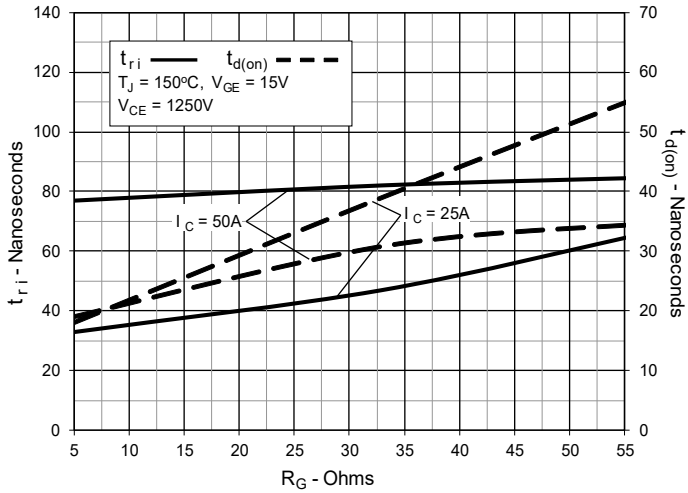
**Fig. 17. Inductive Turn-off Switching Times vs. Collector Current**



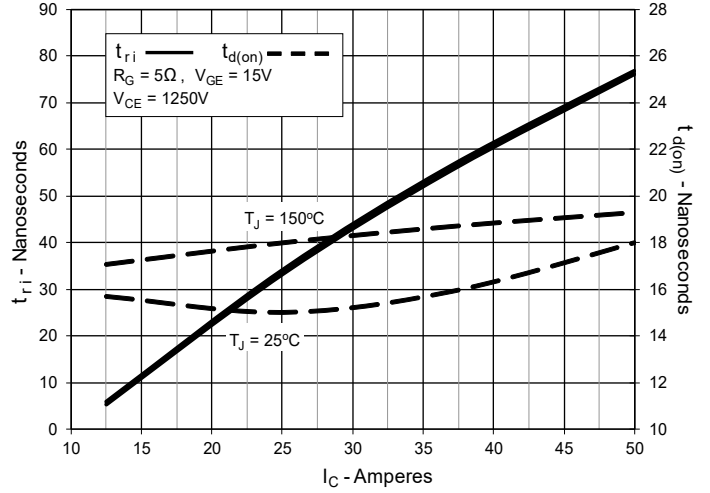
**Fig. 18. Inductive Turn-off Switching Times vs. Junction Temperature**



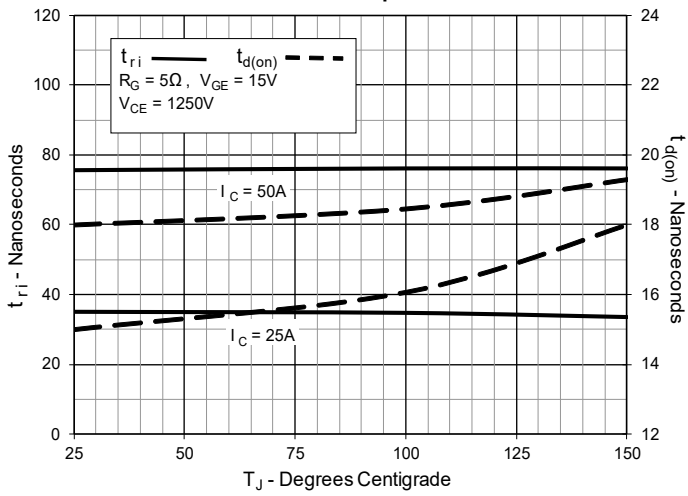
**Fig. 19. Inductive Turn-on Switching Times vs. Gate Resistance**



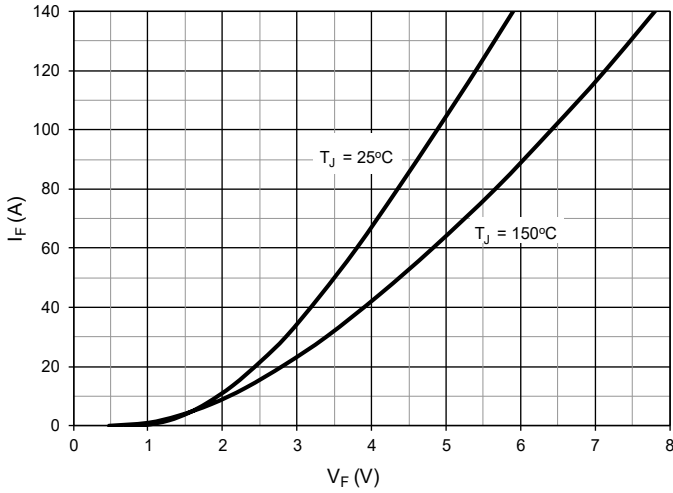
**Fig. 20. Inductive Turn-on Switching Times vs. Collector Current**



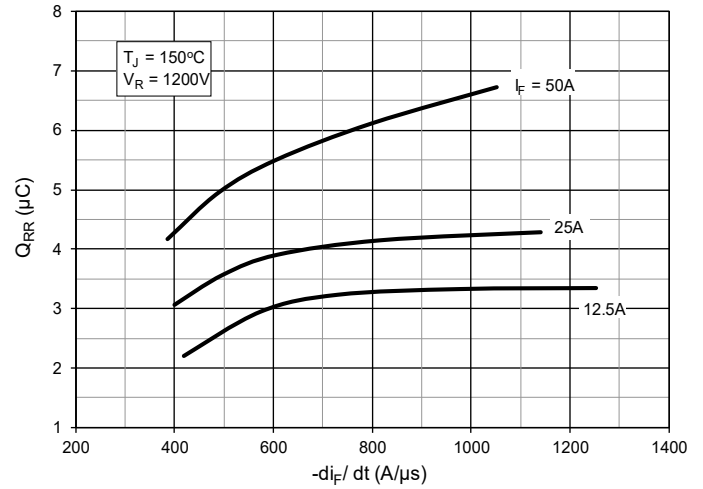
**Fig. 21. Inductive Turn-on Switching Times vs. Junction Temperature**



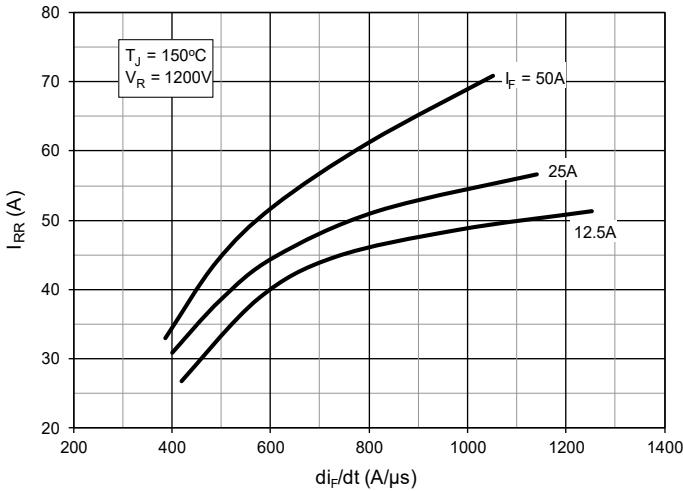
**Fig. 22. Diode Forward Characteristics**



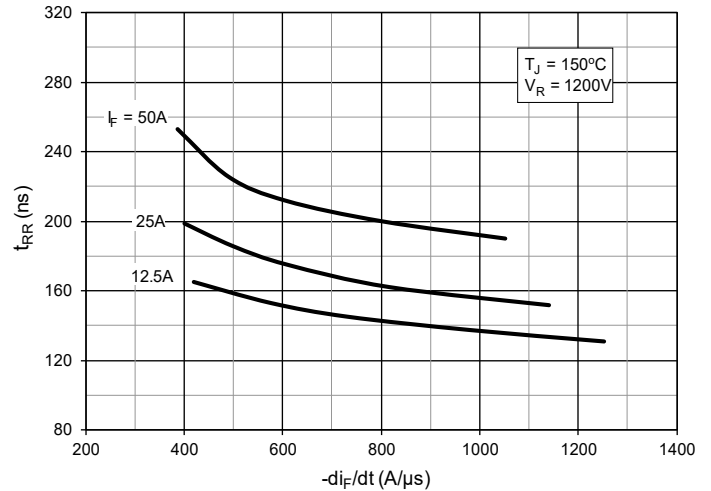
**Fig. 23. Reverse Recovery Charge vs.  $-di_F/dt$**



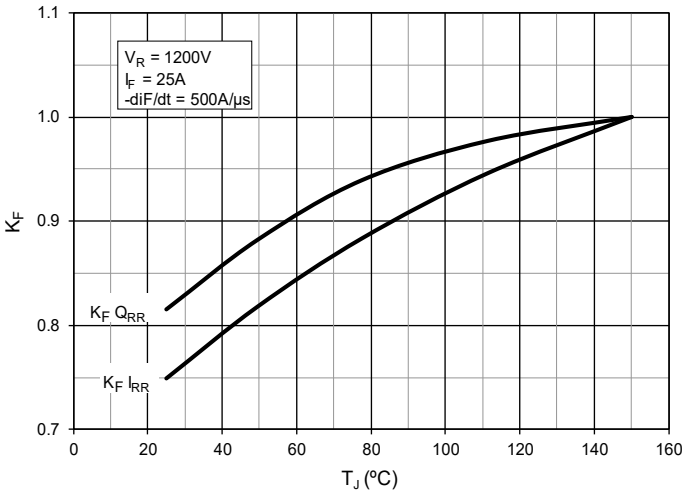
**Fig. 24. Reverse Recovery Current vs.  $-di_F/dt$**



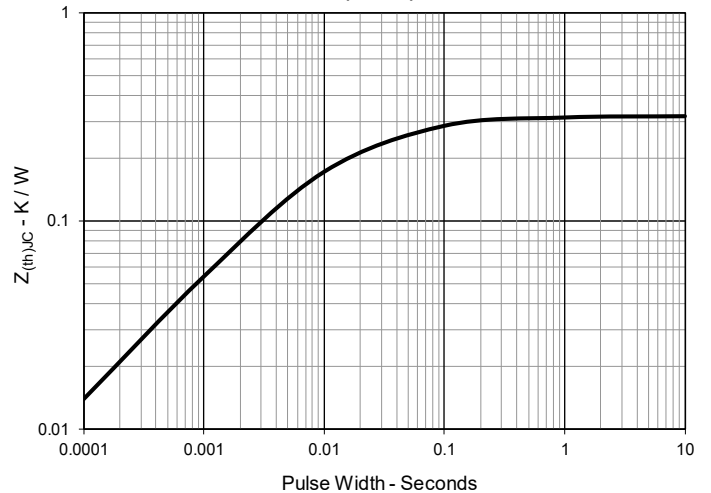
**Fig. 25. Reverse Recovery Time vs.  $-di_F/dt$**

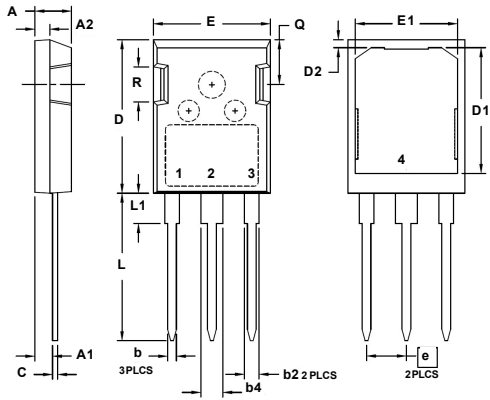


**Fig. 26. Dynamic Parameters  $Q_{RR}$ ,  $I_{RR}$  vs. Junction Temperature**



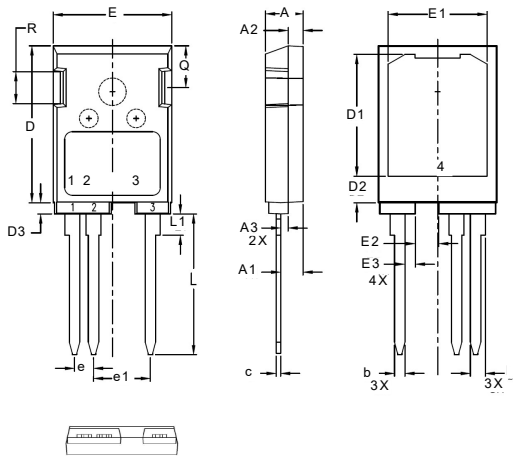
**Fig. 27. Maximum Transient Thermal Impedance (Diode)**



**PLUS247™ Outline**


1 - Gate 3 - Emitter  
 2,4 - Collector

SYM	Inches		Millimeters	
	MIN	MAX	MIN	MAX
A	0.193	0.205	4.83	5.21
A1	0.090	0.100	2.29	2.54
A2	0.075	0.085	1.91	2.16
b	0.045	0.055	1.14	1.40
b2	0.075	0.087	1.91	2.20
b4	0.115	0.126	2.92	3.20
C	0.024	0.031	0.61	0.80
D	0.819	0.840	20.80	21.34
D1	0.650	0.690	16.51	17.53
D2	0.035	0.050	0.89	1.27
E	0.620	0.635	15.75	16.13
E1	0.520	0.560	13.08	14.22
e	0.215	BSC	5.45	BSC
L	0.780	0.810	19.81	20.57
L1	0.150	0.170	3.81	4.32
Q	0.220	0.244	5.59	6.20
R	0.170	0.190	4.32	4.83

**TO-247PLUS-HV Outline**


1 - Gate  
 2,4 - Emitter  
 3 - Collector

SYM	Inches		Millimeters	
	MIN	MAX	MIN	MAX
A	0.193	0.201	4.90	5.10
A1	0.114	0.122	2.90	3.10
A2	0.075	0.083	1.90	2.10
A3	0.035	0.043	0.90	1.10
b	0.053	0.059	1.35	1.50
b1	0.075	0.083	1.90	2.10
c	0.022	0.030	0.55	0.75
D	0.819	0.843	20.8	21.4
D1	0.638	0.646	16.2	16.4
D2	0.134	0.146	3.40	3.70
D3	0.055	0.063	1.40	1.60
E	0.622	0.638	15.8	16.2
E1	0.520	0.528	13.2	13.4
E2	0.118	0.126	3.00	3.20
E3	0.051	0.059	1.30	1.50
e	0.100	BSC	2.54	BSC
e1	0.300	BSC	7.62	BSC
L	0.732	0.748	18.60	19.0
L1	0.106	0.118	2.70	3.00
Q	0.216	0.224	5.50	5.70
R	0.165	0.169	4.20	4.30





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